

PRODUCT FEATURES

- IGBT CHIP(1700V Trench+Field Stop technology)
- Low turn-off losses, short tail current
- $V_{CE(sat)}$ with positive temperature coefficient
- Ultra Low Loss,High Ruggedness
- Free wheeling diodes with fast and soft reverse recovery



APPLICATIONS

- AC motor control
- Motion/servo control
- Inverter and power supplies
- Photovoltaic/Fuel cell

IGBT-inverter

ABSOLUTE MAXIMUM RATINGS($T_C=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter/Test Conditions		Values	Unit
V_{CES}	Collector Emitter Voltage	$T_J=25^{\circ}\text{C}$	1700	V
V_{GES}	Gate Emitter Voltage		± 20	
I_C	DC Collector Current	$T_C=25^{\circ}\text{C}, T_{Jmax}=175^{\circ}\text{C}$	300	A
		$T_C=95^{\circ}\text{C}, T_{Jmax}=175^{\circ}\text{C}$	200	
I_{CM}	Repetitive Peak Collector Current	$t_p=1\text{ms}$	400	
P_{tot}	Power Dissipation Per IGBT	$T_C=25^{\circ}\text{C}, T_{Jmax}=175^{\circ}\text{C}$	1500	W

Diode-inverter

ABSOLUTE MAXIMUM RATINGS ($T_C=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter/Test Conditions		Values	Unit
V_{RRM}	Repetitive Reverse Voltage	$T_J=25^{\circ}\text{C}$	1700	V
$I_{F(AV)}$	Average Forward Current		200	A
I_{FRM}	Repetitive Peak Forward Current	$t_p=1\text{ms}$	400	
I^2t		$T_J=125^{\circ}\text{C}, t=10\text{ms}, V_R=0\text{V}$	6500	A^2S

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MMG200D170B6TC

IGBT-inverter

ELECTRICAL CHARACTERISTICS ($T_C=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter/Test Conditions		Min.	Typ.	Max.	Unit
$V_{GE(th)}$	Gate Emitter Threshold Voltage	$V_{CE}=V_{GE}, I_C=8\text{mA}$	5.0	6.0	6.5	V
$V_{CE(sat)}$	Collector Emitter Saturation Voltage	$I_C=200\text{A}, V_{GE}=15\text{V}, T_J=25^\circ\text{C}$		2.2	2.6	
		$I_C=200\text{A}, V_{GE}=15\text{V}, T_J=125^\circ\text{C}$		2.5		
		$I_C=200\text{A}, V_{GE}=15\text{V}, T_J=150^\circ\text{C}$		2.6		
I_{CES}	Collector Leakage Current	$V_{CE}=1700\text{V}, V_{GE}=0\text{V}, T_J=25^\circ\text{C}$			2	mA
		$V_{CE}=1700\text{V}, V_{GE}=0\text{V}, T_J=150^\circ\text{C}$			20	mA
I_{GES}	Gate Leakage Current	$V_{CE}=0\text{V}, V_{GE}=\pm 20\text{V}, T_J=25^\circ\text{C}$	-500		500	nA
R_{gint}	Integrated Gate Resistor			3		Ω
Q_g	Gate Charge	$V_{CE}=900\text{V}, I_C=200\text{A}, V_{GE}=15\text{V}$		1.6		μC
C_{ies}	Input Capacitance	$V_{CE}=25\text{V}, V_{GE}=0\text{V}, f=1\text{MHz}$		19		nF
C_{res}	Reverse Transfer Capacitance				610	
$t_{d(on)}$	Turn on Delay Time	$V_{CC}=900\text{V}, I_C=200\text{A}$ $R_G=5.1\Omega,$ $V_{GE}=\pm 15\text{V},$ Inductive Load	$T_J=25^\circ\text{C}$	160		ns
			$T_J=150^\circ\text{C}$	180		ns
t_r	Rise Time	$V_{GE}=\pm 15\text{V},$ Inductive Load	$T_J=25^\circ\text{C}$	130		ns
			$T_J=150^\circ\text{C}$	140		ns
$t_{d(off)}$	Turn off Delay Time	$V_{CC}=900\text{V}, I_C=200\text{A}$ $R_G=5.1\Omega,$ $V_{GE}=\pm 15\text{V},$ Inductive Load	$T_J=25^\circ\text{C}$	600		ns
			$T_J=150^\circ\text{C}$	700		ns
t_f	Fall Time	$V_{GE}=\pm 15\text{V},$ Inductive Load	$T_J=25^\circ\text{C}$	200		ns
			$T_J=150^\circ\text{C}$	300		ns
E_{on}	Turn on Energy	$V_{CC}=900\text{V}, I_C=200\text{A}$ $R_G=5.1\Omega,$ $V_{GE}=\pm 15\text{V},$ Inductive Load	$T_J=25^\circ\text{C}$	111		mJ
			$T_J=125^\circ\text{C}$	140		mJ
			$T_J=150^\circ\text{C}$	150		mJ
E_{off}	Turn off Energy	$V_{GE}=\pm 15\text{V},$ Inductive Load	$T_J=25^\circ\text{C}$	34		mJ
			$T_J=125^\circ\text{C}$	52		mJ
			$T_J=150^\circ\text{C}$	56		mJ
I_{SC}	Short Circuit Current	$tpsc \leq 10\mu\text{s}, V_{GE}=15\text{V}$ $T_J=150^\circ\text{C}, V_{CC}=1000\text{V}$		720		A
R_{thJC}	Junction to Case Thermal Resistance (Per IGBT)				0.1	K/W

Diode-inverter

ELECTRICAL CHARACTERISTICS ($T_C=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter/Test Conditions		Min.	Typ.	Max.	Unit
V_F	Forward Voltage	$I_F=200\text{A}, V_{GE}=0\text{V}, T_J=25^\circ\text{C}$		1.8	2.2	V
		$I_F=200\text{A}, V_{GE}=0\text{V}, T_J=125^\circ\text{C}$		1.9		
		$I_F=200\text{A}, V_{GE}=0\text{V}, T_J=150^\circ\text{C}$		1.9		
t_{rr}	Reverse Recovery Time	$I_F=200\text{A}, V_R=900\text{V}$ $di_F/dt=-1100\text{A}/\mu\text{s}$ $T_J=150^\circ\text{C}$		1380		ns
I_{RRM}	Max. Reverse Recovery Current			141		A
Q_{RR}	Reverse Recovery Charge			95		μC
E_{rec}	Reverse Recovery Energy			40		mJ
R_{thJCD}	Junction to Case Thermal Resistance (Per Diode)				0.16	K/W

MMG200D170B6TC

MODULE CHARACTERISTICS ($T_C=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter/Test Conditions	Values	Unit	
T_{Jmax}	Max. Junction Temperature	175	°C	
T_{Jop}	Operating Temperature	-40~150		
T_{stg}	Storage Temperature	-40~125		
V_{isol}	Isolation Breakdown Voltage	AC, 50Hz(R.M.S), t=1minute	4000	V
CTI	Comparative Tracking Index		> 225	
Torque	to heatsink	Recommended (M6)	3~5	Nm
	to terminal	Recommended (M6)	2.5~5	Nm
Weight			300	g

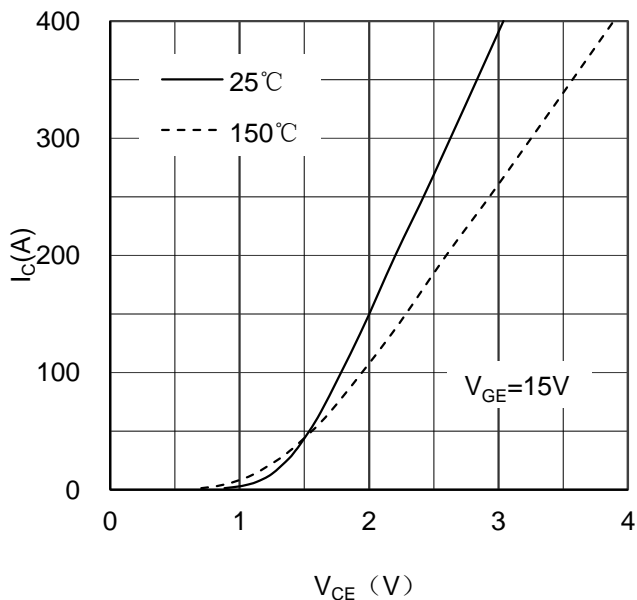


Figure 1. Typical Output Characteristics IGBT-inverter

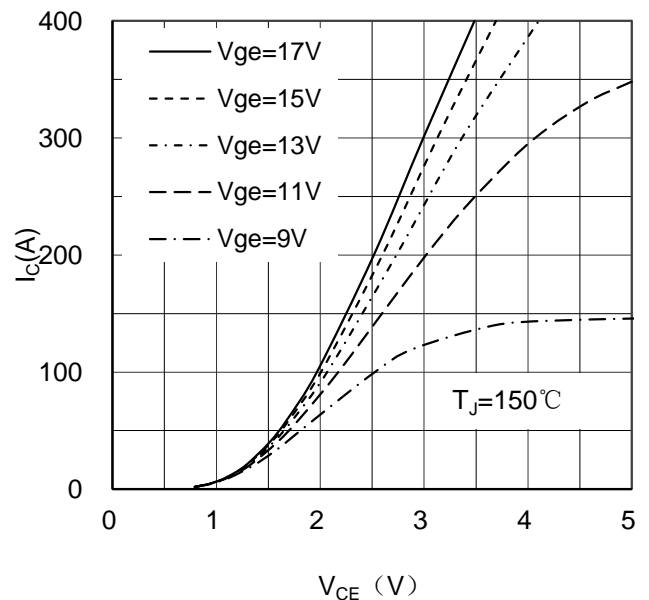


Figure 2. Typical Output Characteristics IGBT-inverter

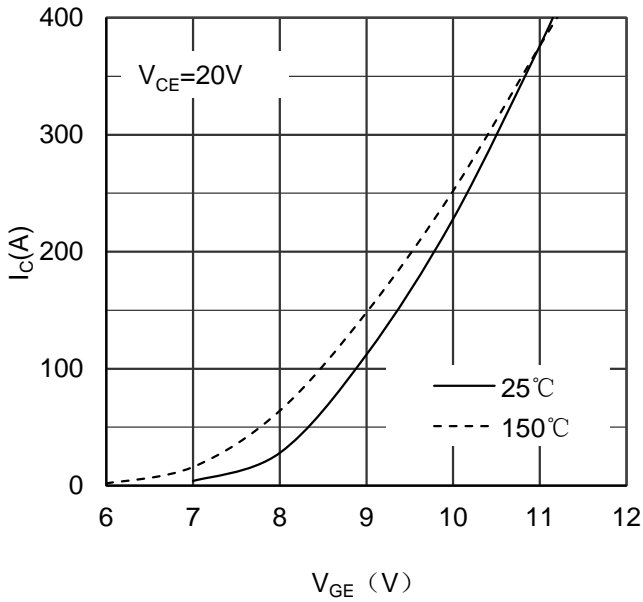


Figure 3. Typical Transfer characteristics IGBT-inverter

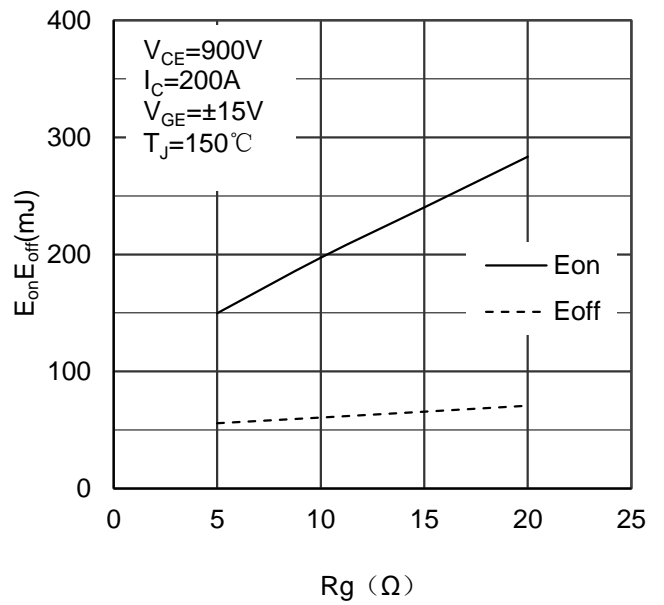


Figure 4. Switching Energy vs Gate Resistor IGBT-inverter

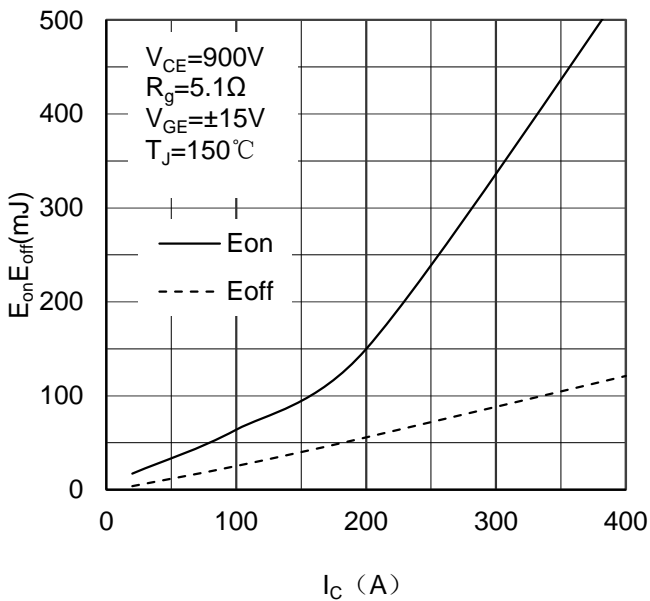


Figure 5. Switching Energy vs Collector Current IGBT-inverter

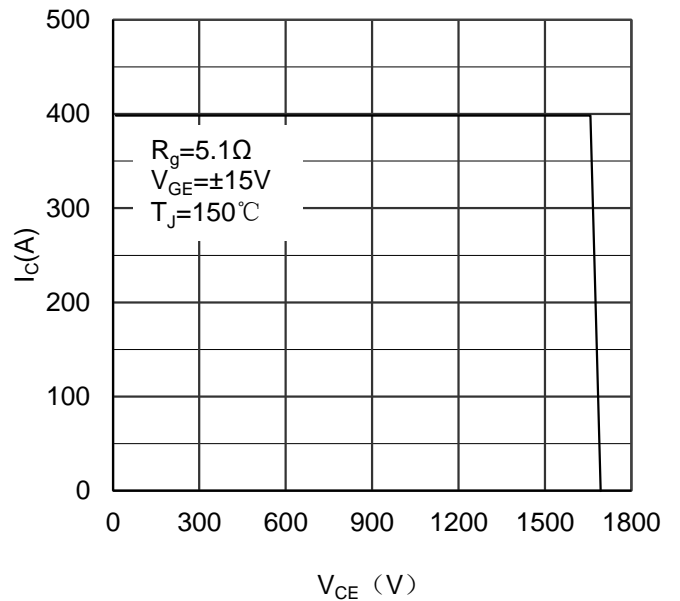


Figure 6. Reverse Biased Safe Operating Area IGBT-inverter

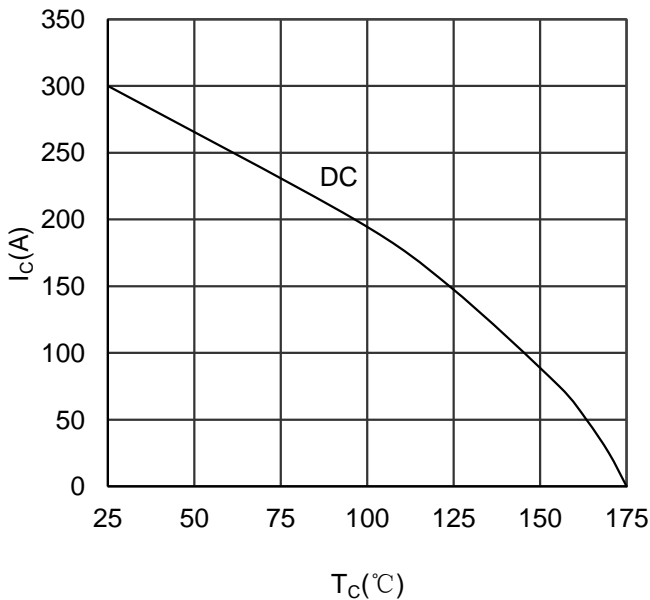


Figure 7. Collector Current vs Case temperature IGBT-inverter

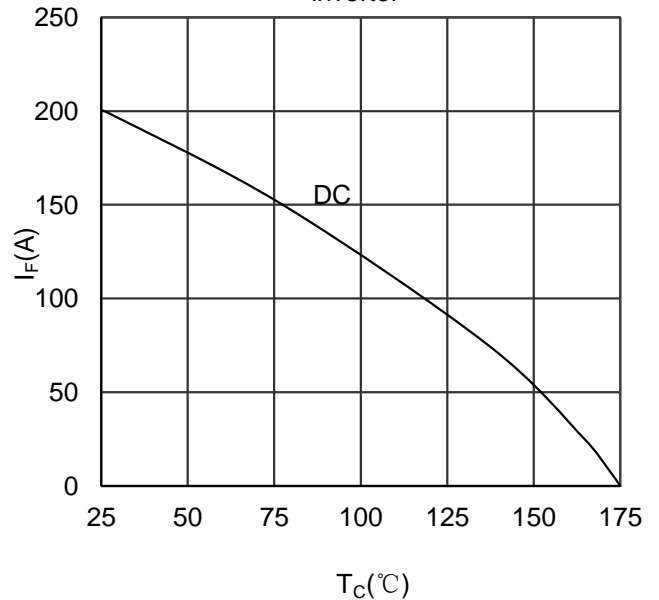


Figure 8. Forward current vs Case temperature Diode-inverter

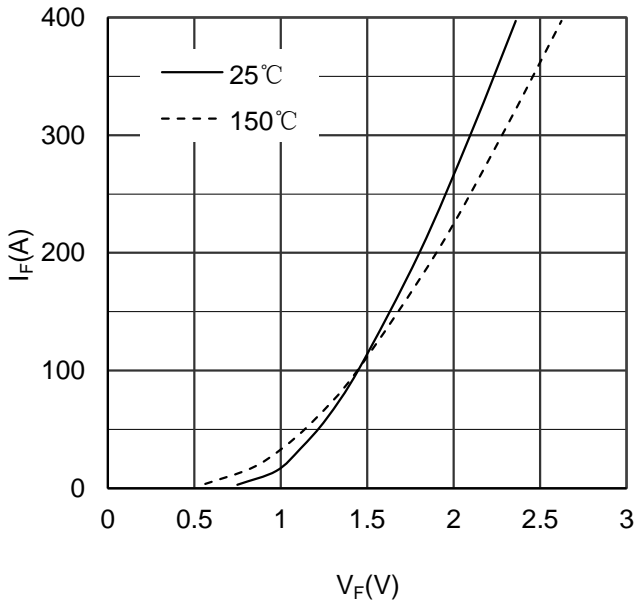


Figure 9. Diode Forward Characteristics Diode -inverter

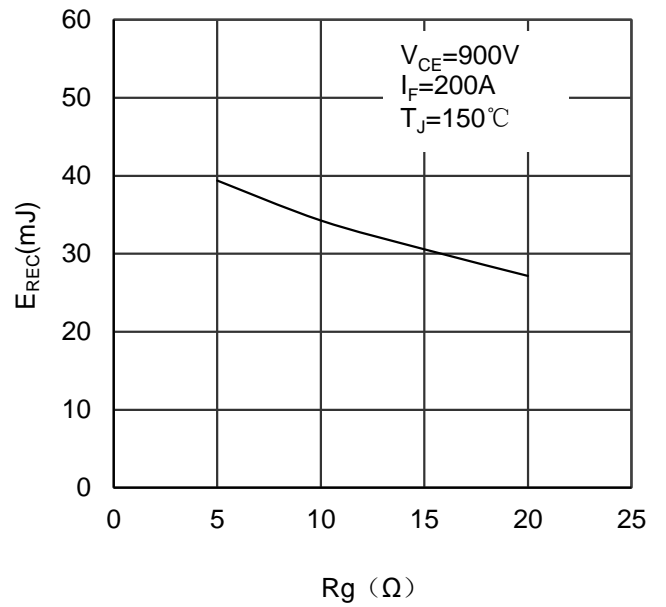


Figure 10. Switching Energy vs Gate Resistor Diode - inverter

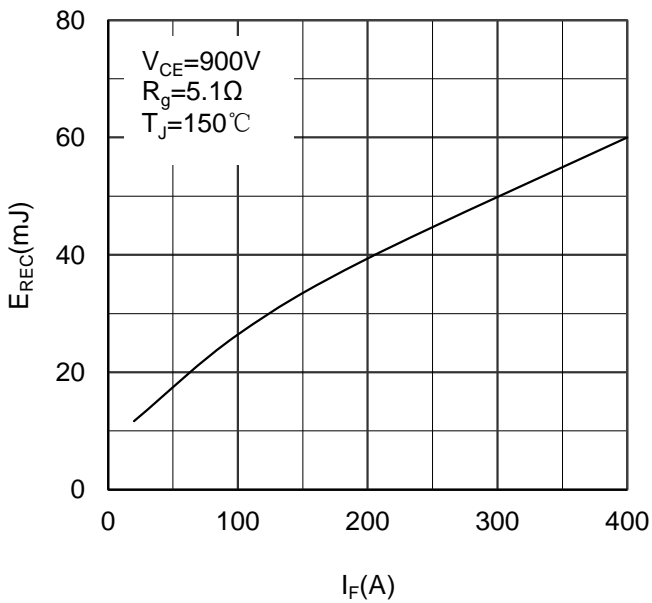


Figure 11. Switching Energy vs Forward Current Diode-inverter

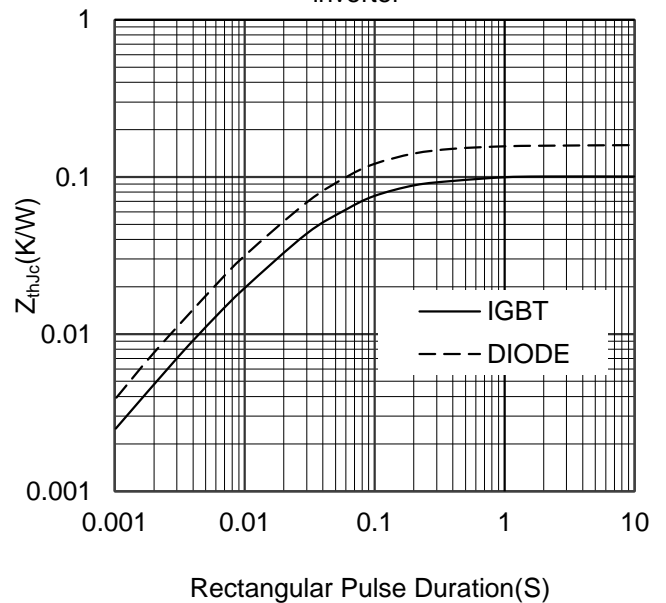


Figure 12. Transient Thermal Impedance of Diode and IGBT-inverter

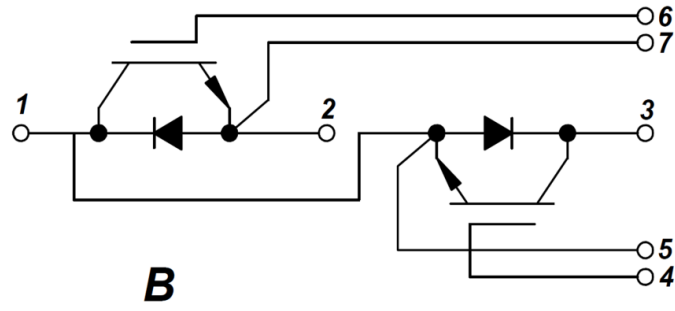


Figure 13. Circuit Diagram

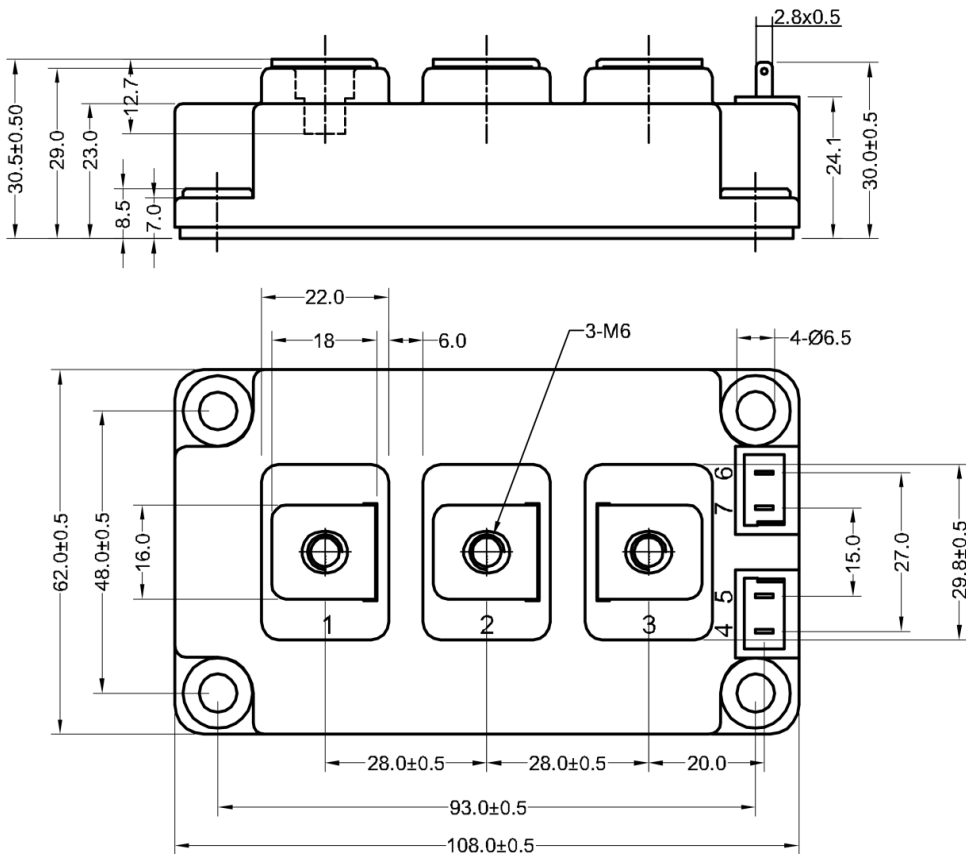


Figure 14. Package Outline